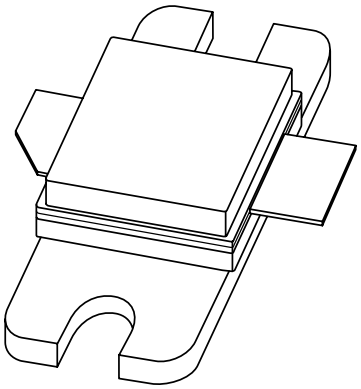
DATA SHEET



BLS3135-50
Microwave power transistor

Product specification
Supersedes data of 1999 Aug 16

2003 Apr 15

Philips
Semiconductors

PHILIPS

Microwave power transistor BLS3135-50

FEATURES

- Suitable for short and medium pulse applications
- Internal input and output matching networks for an easy circuit design
- Emitter ballasting resistors improve ruggedness
- Gold metallization ensures excellent reliability
- Interdigitated emitter-base structure provides high emitter efficiency
- Multicell geometry improves power sharing and reduces thermal resistance.

APPLICATIONS

- Common base class-C pulsed power amplifiers for radar applications in the 3.1 to 3.5 GHz band.

DESCRIPTION

NPN silicon planar epitaxial microwave power transistor in a 2-lead rectangular flange package with a ceramic cap (SOT422A) with the common base connected to the flange.

PINNING - SOT422A

PIN	DESCRIPTION
1	collector
2	emitter
3	base; connected to flange

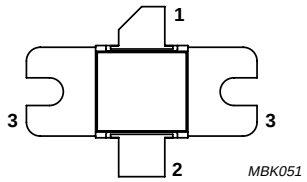


Fig.1 Simplified outline.

QUICK REFERENCE DATA

RF performance at T_h = 25 °C in a common base class-C test circuit.

MODE OF OPERATION	f (GHz)	V_{CB} (V)	P_L (W)	G_p (dB)	η_C (%)
Pulsed, class-C	3.1 to 3.5	40	50	typ. 8	typ. 40

WARNING
Product and environmental safety - toxic materials
This product contains beryllium oxide. The product is entirely safe provided that the BeO disc is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	75	V
V_{CES}	collector-emitter voltage	R_{BE} = 0	–	75	V
V_{EBO}	emitter-base voltage	open collector	–	2	V
I_{CM}	peak collector current	$t_p \leq 100$ μs; $\delta \leq 10\%$	–	6	A
P_{tot}	total power dissipation	t_p = 100 μs; δ = 10%; T_{mb} = 25 °C	–	80	W
T_{stg}	storage temperature		–65	+200	°C
T_j	operating junction temperature		–	200	°C
T_{sld}	soldering temperature	up to 0.2 mm from ceramic cap; $t \leq 10$ s	–	235	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$Z_{th\ j\text{-}h}$	thermal impedance from junction to heatsink	t_p = 100 μs; δ = 10%; note 1	0.71	K/W
		t_p = 300 μs; δ = 10%; note 1	0.99	K/W

Note

1. Equivalent thermal impedance under pulsed microwave operating conditions. Measured with IR-scan with 20 μm spot size at hotspot.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	I_C = 15 mA; open emitter	75	–	V
$V_{(BR)CES}$	collector-emitter breakdown voltage	I_C = 15 mA; V_{BE} = 0	75	–	V
I_{CBO}	collector leakage current	V_{CB} = 40 V; I_E = 0	–	1.5	mA
I_{CES}	collector leakage current	V_{CE} = 40 V; V_{BE} = 0	–	3	mA
I_{EBO}	emitter leakage current	V_{EB} = 1.5 V; I_C = 0	–	0.3	mA
h_{FE}	DC current gain	V_{CB} = 5 V; I_C = 1.5 A	40	–	

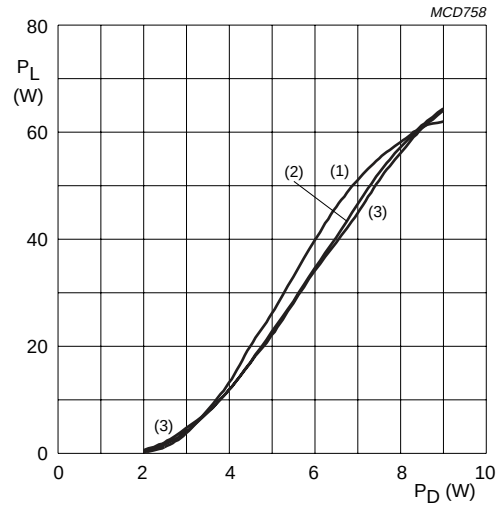
APPLICATION INFORMATION

RF performance at T_h = 25 °C in a common-base test circuit.

MODE OF OPERATION	f (GHz)	V_{CE} (V)	P_L (W)	G_p (dB)	η_C (%)
Class-C; t_p = 100 μs; δ = 10%	3.1 to 3.5	40	≥50 typ. 55	≥7 typ. 8	≥35 typ. 40

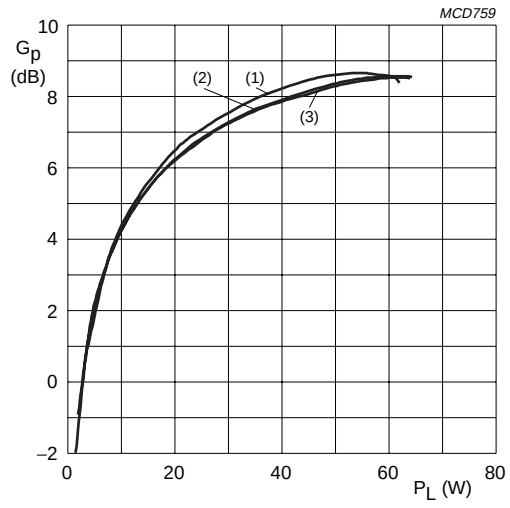
Typical impedance

FREQUENCY (GHZ)	Z_S (Ω)	Z_L (Ω)
3.1	23.5 – j 5.6	7.8 – j 3.7
3.2	23.6 – j 4.3	7.3 – j 4.1
3.3	23.8 – j 2.9	6.6 – j 4.3
3.4	24.3 – j 1.6	5.8 – j 4.2
3.5	24.9 – j 0.3	5.1 – j 4.1



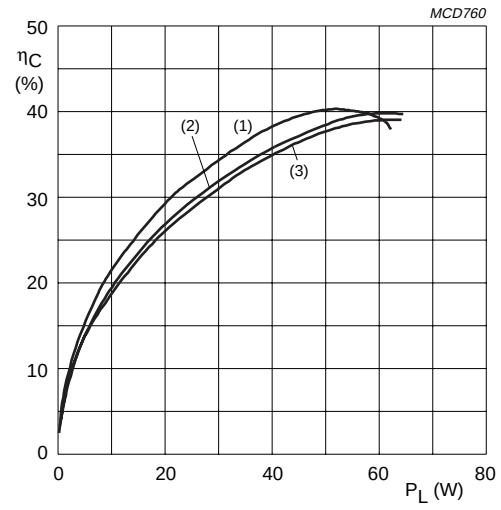
V_{CB} = 40 V; class-C; t_p = 100 µs; δ = 10%.
(1) f = 3.5 GHz.
(2) f = 3.3 GHz.
(3) f = 3.1 GHz.

Fig.2 load power as a function of drive power; typical values.



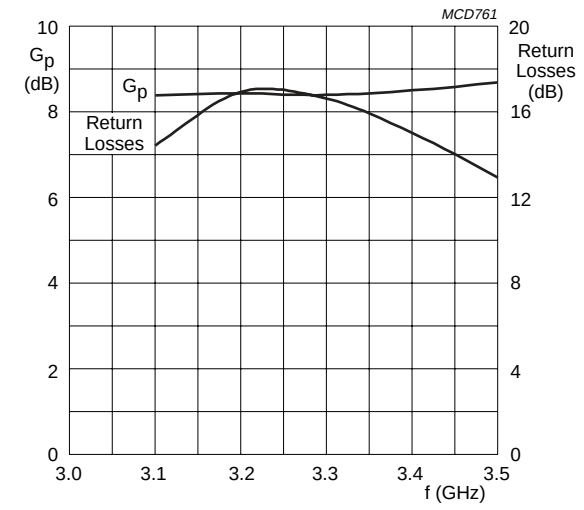
V_{CB} = 40 V; class-C; P_L = 50 W; t_p = 100 µs; δ = 10%.
(1) f = 3.5 GHz.
(2) f = 3.3 GHz.
(3) f = 3.1 GHz.

Fig.3 Power gain as a function of load power; typical values.



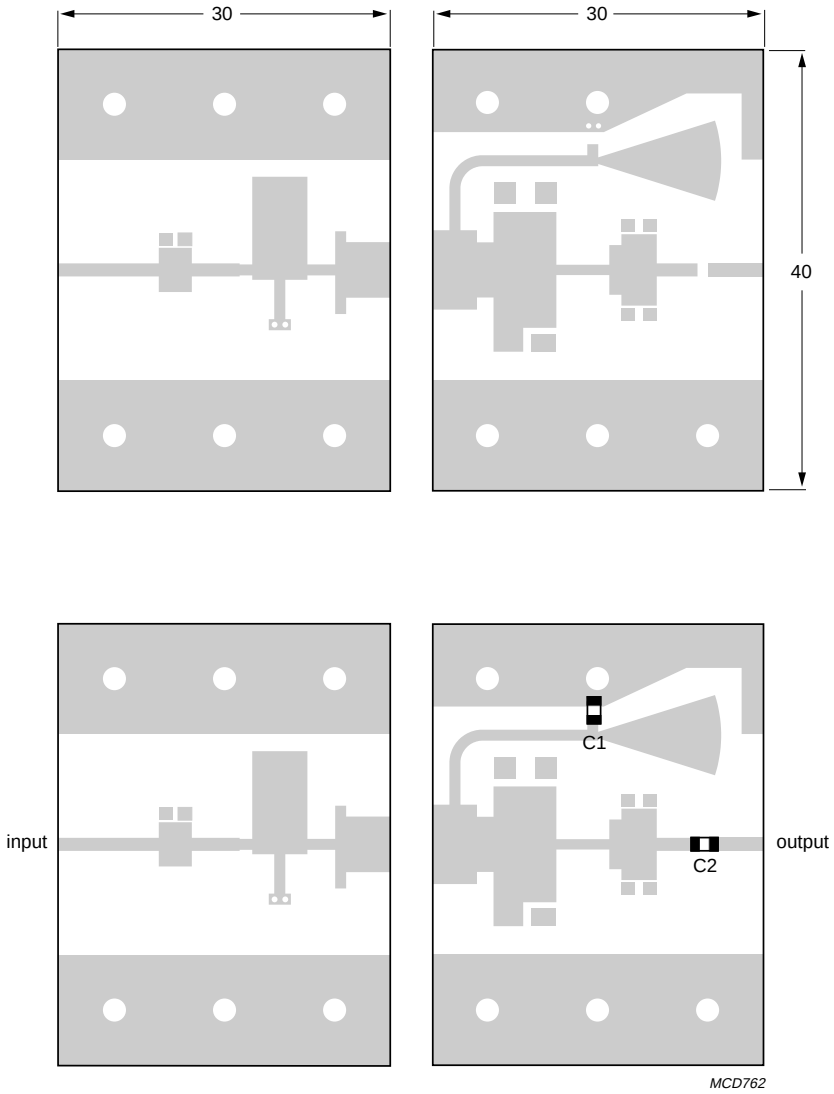
V_{CB} = 40 V; class-C; t_p = 100 µs; δ = 10%.
(1) f = 3.5 GHz.
(2) f = 3.3 GHz.
(3) f = 3.1 GHz.

Fig.4 Collector efficiency as a function of load power; typical values.



V_{CB} = 40 V; class-C; P_L = 50 W; t_p = 100 µs; δ = 10%.

Fig.5 Power gain and input return losses as functions of frequency; typical values.



Dimensions in mm.

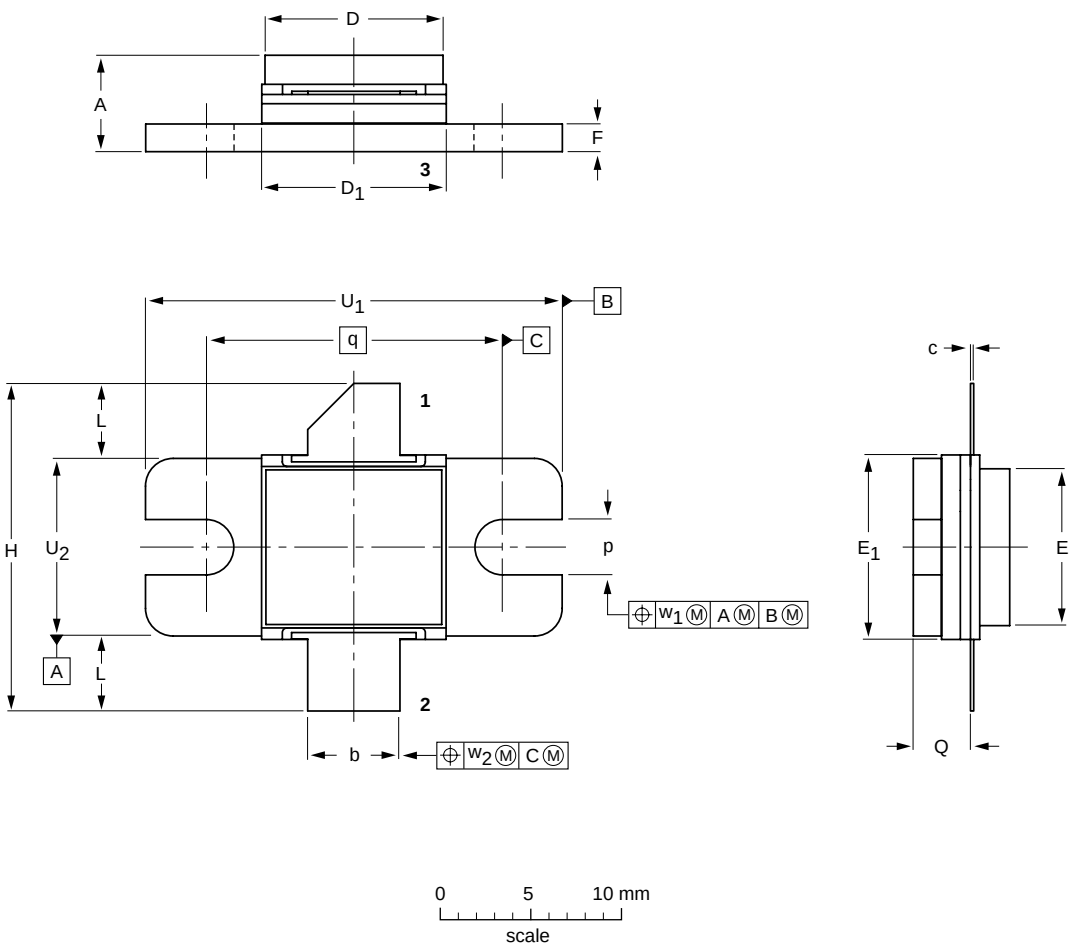
The components are situated on one side of the copper-clad printed-circuit board with Duroid dielectric (ε_r = 2.2), thickness 0.38 mm. The other side is unetched and serves as a ground plane.

C1 = C2 = ATC 100A 5.1 pF

Fig.6 Component layout for 3.1 to 3.5 GHz class-C test circuit.

PACKAGE OUTLINE

Flanged hermetic ceramic package; 2 mounting holes; 2 leads **SOT422A**



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D_1	E	E_1	F	H	L	p	Q	q	U_1	U_2	w_1	w_2
mm	5.72 4.83	5.21 4.95	0.13 0.08	9.93 9.68	10.29 10.03	8.76 8.51	10.29 10.03	1.58 1.47	19.18 17.65	4.52 3.74	3.43 3.18	3.35 2.92	16.51	22.99 22.73	9.91 9.65	0.25	0.76
inches	0.225 0.190	0.205 0.195	0.005 0.003	0.391 0.381	0.405 0.395	0.345 0.335	0.405 0.395	0.062 0.058	0.755 0.695	0.178 0.147	0.135 0.125	0.132 0.115	0.65	0.905 0.895	0.390 0.380	0.01	0.03

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT422A						99-03-29

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS(1)	PRODUCT STATUS(2)(3)	DEFINITION
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